



ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089  
<http://www.nteinc.com>

## NTE6236 Powerblock Module

### **Description:**

The NTE6236 uses 2 high voltage power diodes in series and the semiconductors are electrically isolated from the metal base, allowing common heatsinks and compact assemblies to be built. This device is intended for general purpose applications such as battery chargers, welders and plating equipment and where high voltage and high current are required.

### **Features:**

- High Voltage
- Electrically Isolated Base Plate
- 3000V<sub>RMS</sub> Isolating Voltage
- High Surge Capability
- Large Creepage Distances

### **Ratings and Characteristics:**

Average Forward Current ( $T_C = +100^\circ\text{C}$ , 180° Conduction, Half Sine Wave),  $I_{F(AV)}$  ..... 250A  
 Maximum RMS Forward Current (As AC Switch),  $I_{T(RMS)}$  ..... 393A  
 Maximum Repetitive Peak Reverse Voltage,  $V_{RRM}$  ..... 1600V  
 Maximum Non-Repetitive Peak Reverse Voltage,  $V_{RSM}$  ..... 1700V  
 Maximum Peak Reverse Current ( $T_J = +150^\circ\text{C}$ ),  $I_{RRM}$  ..... 50mA  
 RMS Isolation Voltage (50Hz, Circuit to Base, All Terminals Shorted,  $t = 1\text{s}$ ),  $V_{ISO}$  ..... 3000V  
 Operating Junction Temperature Range,  $T_J$  .....  $-40^\circ$  to  $+150^\circ\text{C}$   
 Storage Temperature Range,  $T_{stg}$  .....  $-40^\circ$  to  $+150^\circ\text{C}$   
 Thermal Resistance, Junction-to-Case (Per Module, DC Operation),  $R_{thJC}$  .....  $0.16^\circ\text{C/W}$   
 Thermal Resistance, Case-to-Sink (Per Module, Note 1),  $R_{thCS}$  .....  $0.02^\circ\text{C/W}$

Note 1. Mounting surface flat, smooth and greased.

### **Electrical Specifications:**

| Parameter  | Symbol    | Test Conditions    |   | Rating | Unit |
|--|-----------|--------------------|---|--------|------|
| Maximum Peak One-Cycle<br>Non-Repetitive Surge Current | $I_{FSM}$ | $t = 10\text{ms}$  | Sinusoidal Half Wave, 100% $V_{RRM}$<br>Reapplied, Initial $T_J = +150^\circ\text{C}$ | 5900   | A    |
|  |           | $t = 8.3\text{ms}$ |   | 6180   | A    |
|  |           | $t = 10\text{ms}$  | Sinusoidal Half Wave, No Voltage<br>Reapplied, Initial $T_J = +150^\circ\text{C}$     | 7015   | A    |
|  |           | $t = 8.3\text{ms}$ |   | 7345   | A    |

### Electrical Specifications (Cont'd):

| Parameter                            | Symbol        | Test Conditions   | Rating  | Unit                  |                       |
|--------------------------------------|---------------|---|---|-----------------------|-----------------------|
| Maximum $I^2t$ for Fusing            | $I^2t$        | t = 10ms  | Sinusoidal Half Wave, 100% $V_{RRM}$<br>Reapplied, Initial $T_J = +150^\circ\text{C}$ | 174                   | $\text{kA}^2\text{s}$ |
|                                      |               | t = 8.3ms   |   | 159                   | $\text{kA}^2\text{s}$ |
|                                      |               | t = 10ms  | Sinusoidal Half Wave, No Voltage<br>Reapplied, Initial $T_J = +150^\circ\text{C}$     | 246                   | $\text{kA}^2\text{s}$ |
|                                      |               | t = 8.3ms   |   | 225                   | $\text{kA}^2\text{s}$ |
| Maximum $I^2\sqrt{t}$                | $I^2\sqrt{t}$ | t = 0.1 to 10ms, no voltage reapplied   | 2460  | $\text{kA}^2\sqrt{t}$ |                       |
| Threshold Voltage, Low level         | $V_{F(TO)1}$  | $T_J = +150^\circ\text{C}$ , $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$  | 0.79  | V                     |                       |
| Threshold Voltage, High level        | $V_{F(TO)2}$  | $T_J = +150^\circ\text{C}$ , $(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)})$  | 0.92  | V                     |                       |
| Forward Slope Resistance, Low Level  | $r_{f1}$      | $T_J = +150^\circ\text{C}$ , $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$  | 0.63  | $\text{m}\Omega$      |                       |
| Forward Slope Resistance, High Level | $r_{f2}$      | $T_J = +150^\circ\text{C}$ , $(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)})$  | 0.49  | $\text{m}\Omega$      |                       |
| Maximum Forward Voltage Drop         | $V_{FM}$      | $T_J = +25^\circ\text{C}$ , $I_{FM} = \pi \times I_{F(AV)}$ ,<br>Av. Power = $V_{F(TO)} \times I_{T(AV)} + r_f \times (I_{F(RMS)})^2$ | 1.29  | V                     |                       |

### Circuit Diagram

